L Number	Hits	Search Text	DB	Time stamp
Number 1	8	9440824 "9440822"	HCDAT:	2002/00/09
•	•	9410821, "9410822"	USPAT;	2003/09/08 09:43
			US-PGPUB;	U3:43
			EPO; JPO;	
			DERWENT;	
2		(0.440.024 H0.440.022H) and man add a sure	IBM_TDB	0000/00/00
2	1	(9410821, "9410822") and gas adj2 sensor	USPAT;	2003/09/08
			US-PGPUB;	09:52
			EPO; JPO;	
			DERWENT;	
_	_	(0.440.004 U0.440.000U) I	IBM_TDB	2222/22/22
3	1	(9410821, "9410822") and gas near3 sensor	USPAT;	2003/09/08
			US-PGPUB;	09:51
			EPO; JPO;	
			DERWENT;	
		(manfat with man adia annua) and bathata	IBM_TDB	2002/20/22
6	0	(mosfet with gas adj2 sensor) and hot\$plate	USPAT;	2003/09/08
			US-PGPUB;	10:36
			EPO; JPO;	
			DERWENT;	
_			IBM_TDB	0000100100
7	0	(mosfet with gas adj2 sensor) and hotplate	USPAT;	2003/09/08
			US-PGPUB;	09:51
			EPO; JPO;	
			DERWENT;	
	46	(hadalada and abandada adi assas )	IBM_TDB	0000/00/00
9	16	(hotplate and chemical adj sensor) and gas	USPAT;	2003/09/08
		near3 sensor	US-PGPUB;	10:02
			EPO; JPO;	
			DERWENT;	
10	13	(hetalate and showing and according	IBM_TDB	2002/00/00
.0	13	(hotplate and chemical adj sensor) and gas adj2 sensor	USPAT;	2003/09/08
		aujz sensor	US-PGPUB;	10:27
			EPO; JPO;	
			DERWENT;	
11	18	(hotplate and chemical adj sensor) and	IBM_TDB USPAT;	2003/09/08
• •	.5	membrane	US-PGPUB;	10:18
	İ		EPO; JPO;	10.10
			DERWENT;	
			IBM_TDB	
12	0	(mosfet with gas adj2 sensor) and 219/461	USPAT;	2003/09/08
•-		min gas aujz schsolj aliu 213/401	US-PGPUB;	10:07
			EPO; JPO;	10:07
			DERWENT;	
			IBM_TDB	
13	o	(hotplate and chemical adj sensor) and	_	2002/00/06
		219/461	USPAT;	2003/09/08
		2 1 3/70 1	US-PGPUB;	10:07
			EPO; JPO;	ĺ
			DERWENT;	
			IBM_TDB	

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15	17	((mosfet with gas adj2 sensor) and	USPAT;	2003/09/08
		membrane) and chemical adj2 sensor	US-PGPUB;	10:36
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
14	18	(mosfet with gas adj2 sensor) and	USPAT;	2003/09/08
		membrane	US-PGPUB;	10:12
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
16	15	((hotplate and chemical adj sensor) and gas	USPAT;	2003/09/08
		near3 sensor) and membrane	US-PGPUB;	11:59
		nears sensory and membrane	EPO; JPO;	11.55
			DERWENT;	
			IBM_TDB	
4	1	(9410821, "9410822") and gas with sensor	_	2003/09/08
-	<b>1</b>	(3410021, 3410022 ) and gas with sensor	USPAT;	
			US-PGPUB;	10:25
			EPO; JPO;	
			DERWENT;	
4-	40	//	IBM_TDB	
17	13	(hotplate and chemical adj sensor) and gas	USPAT;	2003/09/08
		adj sensor	US-PGPUB;	10:36
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
20	0	(219/461 and hot\$plate) and gas adj sensor	USPAT;	2003/09/08
			US-PGPUB;	10:36
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
21	0	(219/461 and hot\$plate) and chemical adj2	USPAT;	2003/09/08
		sensor	US-PGPUB;	10:36
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
19	42	219/461 and hot\$plate	USPAT;	2003/09/08
			US-PGPUB;	10:36
			EPO; JPO;	
			DERWENT;	
1			IBM_TDB	
22	1 1	(219/461 and hot\$plate) and membrane	USPAT;	2003/09/08
			US-PGPUB;	10:37
			EPO; JPO;	
1			DERWENT;	
			IBM_TDB	
23	22	(219/461 and hot\$plate) and sensor	USPAT;	2003/09/08
		•	US-PGPUB;	10:45
			EPO; JPO;	
			DERWENT;	
1			IBM_TDB	

24	0	((219/461 and hot\$plate) and sensor) and	USPAT;	2003/09/08
		micro	US-PGPUB;	10:39
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
25	o	((219/461 and hot\$plate) and membrane)	USPAT;	2003/09/08
		and mosfet	US-PGPUB;	10:46
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
5	40	mosfet with gas adj2 sensor	USPAT;	2003/09/08
"		mosiet with gas aujz sensor	1	
			US-PGPUB;	10:48
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
26	0	(((hotplate and chemical adj sensor) and gas	USPAT;	2003/09/08
		near3 sensor) and membrane) and	US-PGPUB;	10:58
		membrane with insulator	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
27	0	((mosfet with gas adj2 sensor) and	USPAT;	2003/09/08
	]	membrane) and membrane with insulator	US-PGPUB;	10:59
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
28	o	((hotplate and chemical adj sensor) and	USPAT;	2003/09/08
		membrane) and membrane with insulator	US-PGPUB;	10:59
		,	EPO; JPO;	1000
			DERWENT;	
			IBM_TDB	
29	o	(hotplate and chemical adj sensor) and	USPAT;	2003/09/08
		membrane with insulator	US-PGPUB;	10:59
		monibiano with modiator	EPO; JPO;	10.33
			DERWENT;	
			, and a second s	
30	0	(9410821, "9410822") and membrane with	IBM_TDB	2003/09/08
	"	insulator	USPAT;	
		iliouiatur	US-PGPUB;	10:59
			EPO; JPO;	
			DERWENT;	
24	_	hadalada ada a da a da a	IBM_TDB	
31	6	hotplate and membrane with insulator	USPAT;	2003/09/08
		<b>q</b>	US-PGPUB;	11:04
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
32	0	(hotplate and membrane with insulator) and	USPAT;	2003/09/08
		masking and etching	US-PGPUB;	11:06
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

33   2   (hotplate and membrane with insulator) and etching	Setching					
361418	361418   (hotplate and membrane with insulator) and masking or etching   USPAT;	33	2		,	2003/09/08
361418	361418			etching	US-PGPUB;	11:05
361418   (hotplate and membrane with insulator) and masking or etching   US-PGPUB; EPO; JPO; DERWENT; IBM_TDB   USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	361418				EPO; JPO;	
361418   (hotplate and membrane with insulator) and masking or etching   US-PGPUB; EPO; JPO; DERWENT; IBM_TDB   USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	361418				DERWENT;	
361418	361416   (hotplate and membrane with insulator) and masking or etching   USPAT; US-PGPUB; EPC; JPO; DERWENT; IBM_TDB US-PGPUB; IDS-PGPUB; IDS-P				IBM TDB	
Masking or etching	Masking or etching	34	361418	(hotplate and membrane with insulator) and	_	2003/09/08
Second   S	September   Sept			, ,	-	
35   0   (hotplate and membrane with insulator) and masking   USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; IBM TDB USPAT	1			masking or otoming		
18	18M_TDB				1 '	
35	35					
Masking	Masking	25		(hetalete and membrane with insulator) and	_	2022/20/20
Second Color   Seco	September   Sept	35		•	,	
36   0   (mosfet with gas adj2 sensor) and masking   DERWENT;   IBM_TDB   USPAT;   US-PGPUB;   EPO; JPO;   DERWENT;   IBM_TDB   USPAT;   US-PGPUB;   US-PG	13			masking	,	11:07
18	18M_TDB					
36	36				·	
11:07	11:07				_	
Seporate	Second	36	0	(mosfet with gas adj2 sensor) and masking	,	2003/09/08
DERWENT;   IBM_TDB   USPAT;   2003/09/08   USPAT;   USPGPUB;   USPGPUB;   EPO; JPO;   DERWENT;   IBM_TDB   USPAT;   USPGPUB;   EPO; JPO;   USPGPUB;   USP	37   6   219/461 and masking   DERWENT;   IBM_TDB   USPAT;   USPAT;   USPAT;   USPGPUB;   EPO; JPO;   DERWENT;   IBM_TDB   USPAT;   USPA				US-PGPUB;	11:07
Same	18M_TDB				EPO; JPO;	
37   6   219/461 and masking   USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB   USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB   USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB   USPAT; IBM_TDB   USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; IBM_TDB   USPAT; USPAPUB; EPO; JPO; DERWENT; IBM_TDB   USPAT; USPO; USPAT; USPAT	37   6   219/461 and masking   USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB   USPAT; US-PGPUB; US-PGP	1			DERWENT;	
11:09   US-PGPUB;   EPO; JPO;   DERWENT;   IBM_TDB   EPO;   DERWENT;   IBM_	13   (hotplate and chemical adj sensor) and   US-PGPUB;   EPO; JPO;   DERWENT;   IBM_TDB   USPAT;   US-PGPUB;   US-PGP				IBM_TDB	
13	13	37	6	219/461 and masking	USPAT;	2003/09/08
13	13   (hotplate and chemical adj sensor) and masking   DERWENT;   IBM_TDB   USPAT;			-	US-PGPUB;	11:09
13	13   (hotplate and chemical adj sensor) and masking   DERWENT;   IBM_TDB   USPAT;				EPO; JPO;	
13	13					
13	13				1	
masking   US-PGPUB;   EPO; JPO;   DERWENT;   IBM_TDB   US-PGPUB;   US-PGPUB;   US-PGPUB;   US-PGPUB;   EPO; JPO;   DERWENT;   IBM_TDB   USPAT;   US-PGPUB;   US-PGPUB;   US-PGPUB;   EPO; JPO;   DERWENT;   IBM_TDB   US-PGPUB;   EPO; JPO;   DERWENT;   IBM_TDB   USPAT;   USP	Masking	38	13	(hotplate and chemical adi sensor) and		2003/09/08
### Second Control of the Image	Sepoint   Sepo				1	
DERWENT; IBM_TDB USPAT; 2003/09/08 US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; 2003/09/08 USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	39   0   hotplate same sensor same masking   DERWENT;   IBM_TDB   USPAT;   US-PGPUB;   EPO; JPO;   DERWENT;   IBM_TDB   USPAT;   US-PGPUB;   EPO; JPO;   DERWENT;   IBM_TDB   USPAT;   US-PGPUB;   EPO; JPO;   DERWENT;   IBM_TDB   USPAT;   IBM_TDB   USPAT;   IBM_TDB   USPAT;   USPAT			•		
39 0 hotplate same sensor same masking USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	18	1				
18	18					
US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USP	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; II:24	39	0	hotolate same, sensor same macking	_	2003/09/08
## EPO; JPO; DERWENT; IBM_TDB  ## USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB  ## USPAT; USPA	40 18 hotplate same masking			notplate dame delicer dame masking	•	
40 18 hotplate same masking USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB 41 4 ((219/461 and hot\$plate) and sensor) and diode USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US	40 18 hotplate same masking USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;				•	11.17
40 18 hotplate same masking USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	40 18 hotplate same masking USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; US-PGPUB; 11:24					
40  18 hotplate same masking  USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPAT; US-PGPUB; EPO; JPO; DERWENT; USPAT; USPA	40 18 hotplate same masking USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; Adj2 sensor) and diode US-PGPUB; 11:24				·	
4 ((219/461 and hot\$plate) and sensor) and diode  ((219/461 and hot\$plate) and sensor) and diode  US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	41 4 ((219/461 and hot\$plate) and sensor) and diode US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; adj2 sensor) and diode US-PGPUB; US-PGPUB; 11:24	40	4.0	hotplata sama maskira		2002/00/00
41 4 ((219/461 and hot\$plate) and sensor) and diode EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	41 4 ((219/461 and hot\$plate) and sensor) and diode US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; adj2 sensor) and diode US-PGPUB; US-PGPUB; 11:24	70	'6	nothiate same masking	•	
41 4 ((219/461 and hot\$plate) and sensor) and diode USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	41 4 ((219/461 and hot\$plate) and sensor) and diode USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB  42 0 ((hotplate and chemical adj sensor) and gas adj2 sensor) and diode USPAT; US-PGPUB; US-PGPUB; 11:24				1	11:21
41 4 ((219/461 and hot\$plate) and sensor) and diode USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	41 4 ((219/461 and hot\$plate) and sensor) and diode USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB  42 0 ((hotplate and chemical adj sensor) and gas adj2 sensor) and diode USPAT; US-PGPUB; 11:24				1 ' '	
41 4 ((219/461 and hot\$plate) and sensor) and diode USPAT; 2003/09/08 11:24 EPO; JPO; DERWENT; IBM_TDB	4 ((219/461 and hot\$plate) and sensor) and diode  USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB  USPAT; USPAT					
diode US-PGPUB; 11:24 EPO; JPO; DERWENT; IBM_TDB	diode  US-PGPUB; EPO; JPO; DERWENT; IBM_TDB  ((hotplate and chemical adj sensor) and gas adj2 sensor) and diode  US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; 11:24					
EPO; JPO; DERWENT; IBM_TDB	42 0 ((hotplate and chemical adj sensor) and gas adj2 sensor) and diode  EPO; JPO; DERWENT; IBM_TDB USPAT; 2003/09/08 US-PGPUB; 11:24	41	4			
DERWENT; IBM_TDB	42 0 ((hotplate and chemical adj sensor) and gas adj2 sensor) and diode DERWENT; IBM_TDB USPAT; 2003/09/08 11:24			diode		11:24
IBM_TDB	42 0 ((hotplate and chemical adj sensor) and gas adj2 sensor) and diode IBM_TDB USPAT; 2003/09/08 11:24					
	0 ((hotplate and chemical adj sensor) and gas adj2 sensor) and diode USPAT; 2003/09/08 11:24				,	
	adj2 sensor) and diode US-PGPUB; 11:24				IBM_TDB	
42 0 ((hotplate and chemical adj sensor) and gas USPAT; 2003/09/08		42	0	((hotplate and chemical adj sensor) and gas	USPAT;	2003/09/08
adj2 sensor) and diode US-PGPUB;   11:24	EPO: JPO:		,	adj2 sensor) and diode	US-PGPUB;	11:24
EPO; JPO;					EPO; JPO;	
	DERWENT;					
			i			
DERWENT;			1		IBM_TDB	

43	1	(hotplate and chemical adj sensor) and	USPAT;	2003/09/08
		diode	US-PGPUB;	11:25
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
8	24	hotplate and chemical adj sensor	USPAT;	2003/09/08
			US-PGPUB;	11:50
			EPO; JPO;	1
			DERWENT;	
			IBM_TDB	
18	269	219/461	USPAT;	2003/09/08
.0			US-PGPUB;	11:52
			EPO; JPO;	11.52
			DERWENT;	
44	12	///betalate and shawing! adi assess) and ass	IBM_TDB	0000/00/00
44	12	(((hotplate and chemical adj sensor) and gas	USPAT;	2003/09/08
:		near3 sensor) and membrane) and substrate	US-PGPUB;	12:11
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
45	1	((((hotplate and chemical adj sensor) and	USPAT;	2003/09/08
		gas near3 sensor) and membrane) and	US-PGPUB;	12:12
		substrate) and silicon adj carbide	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
46	1	(hotplate and chemical adj sensor) and	USPAT;	2003/09/08
		silicon adj carbide	US-PGPUB;	12:13
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
47	1	((hotplate and chemical adj sensor) and gas	USPAT;	2003/09/08
		near3 sensor) and silicon adj carbide	US-PGPUB;	12:15
		-	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
48	O	(mosfet with gas adj2 sensor) and silicon	USPAT;	2003/09/08
		adj carbide	US-PGPUB;	12:13
		-	EPO; JPO;	
	1		DERWENT;	
			IBM_TDB	
49	5839	semiconductor with silicon adj carbide	USPAT;	2003/09/08
		oomoonaactor with omoon aaj carbiac	US-PGPUB;	12:14
			EPO; JPO;	12.14
			DERWENT;	
			1	
50	6	(comiconductor with ciliagn adi aarbida)d	IBM_TDB	2002/00/00
30	"	(semiconductor with silicon adj carbide) and hotplate	USPAT;	2003/09/08
		notpiate	US-PGPUB;	12:15
			EPO; JPO;	
			DERWENT;	
	L		IBM_TDB	

51	12	(semiconductor with silicon adj carbide) and	USPAT;	2003/09/08
		hot\$plate	US-PGPUB;	12:32
		-	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
52	49	4203138, "4234361"	USPAT;	2003/09/08
			US-PGPUB;	12:35
	•		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
54	10	((4203138, "4234361") and hydroxide) and	USPAT;	2003/09/08
		ion	US-PGPUB;	12:38
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
55	2	((4203138, "4234361") and hydroxide) and	USPAT;	2003/09/08
		etching with ion	US-PGPUB;	12:51
		-	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
53	13	(4203138, "4234361") and hydroxide	USPAT;	2003/09/08
			US-PGPUB;	12:38
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
56	23	(mosfet with gas adj2 sensor) and sensor	USPAT;	2003/09/08
		with metal adj oxide	US-PGPUB;	12:52
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
57	21	((mosfet with gas adj2 sensor) and sensor	USPAT;	2003/09/08
		with metal adj oxide) and sensor with	US-PGPUB;	12:52
		polymer	EPO; JPO;	
			DERWENT;	
			IBM_TDB	